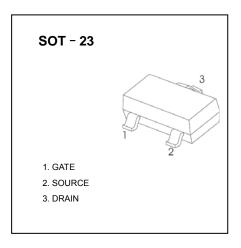
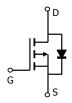


#### **P-Channel MOSFET**

#### **Features**

- VDS (V) =-30V
- ID =-4.2 A (VGS =-10V)
- ullet RDS(ON) < 50m  $\Omega$  (VGS =-10V)
- RDS(ON) < 65m  $\Omega$  (VGS =-4.5V)





#### **Absolute Maximum Ratings** Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	VDS	-30	V	
Gate-Source Voltage	Vgs	±12		
Continuous Drain Current Ta = 25℃	Ιp	-4.2	А	
Ta = 70℃	ID.	-3.5		
Pulsed Drain Current	Ірм	-30		
Power Dissipation Ta = 25 ℃	Pp	1.4	W	
Ta = 70℃	FD	1	VV	
Thermal Resistance.Junction- to-Ambient $t \le 10s$	RthJA	90	°C/W	
Thermal Resistance.Junction- to-Ambient	Kinja	125		
Thermal Resistance.Junction- to-Case	RthJC	60		
Junction Temperature	TJ	150	$^{\circ}$ C	
Junction and Storage Temperature Range	Tstg	-40 to 105	C	



#### **Electrical Characteristics** Ta = 25 °C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID=-250 µ A, VGS=0V				V
Zana Onto Welfano Brain Overset	IDSS	VDS=-24V, VGS=0V			-1	^
Zero Gate Voltage Drain Current		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55℃			-5	μА
Gate-Body leakage current	Igss	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			$\pm100$	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS ID=-250 μ A	-0.4		-1.3	V
Static Drain-Source On-Resistance	Rds(on)	Vgs=-10V, ID=-4.2A			50	mΩ
		Vgs=-4.5V, ID=-4A			65	
On state drain current	ID(ON)	Vgs=-4.5V, Vds=-5V	-25			Α
Forward Transconductance	grs	VDS=-5V, ID=-5A	7	11		S
Input Capacitance	Ciss	Vgs=0V, Vds=-15V, f=1MHz		954		pF
Output Capacitance	Coss			115		
Reverse Transfer Capacitance	Crss			77		
Gate resistance	Rg	Vgs=0V, Vps=0V, f=1MHz		6		Ω
Total Gate Charge	Qg			9.4		
Gate Source Charge	Qgs	Vgs=-4.5V, Vds=-15V, Id=-4A		2		nC
Gate Drain Charge	Qgd			3		
Turn-On DelayTime	td(on)			6.3		
Turn-On Rise Time	tr	VGS=-10V, VDS=-15V, RL=3.6 $\Omega$ ,RGEN=6 $\Omega$ IF=-4A, di/dt=100A/ $\mu$ s		3.2		ns
Turn-Off DelayTime	td(off)			38.3		
Turn-Off Fall Time	tf			12		
Body Diode Reverse Recovery Time	trr			20.2		
Body Diode Reverse Recovery Charge	Qrr	IF=5A, dı/dt=100A/ μ s		11.2		nC
Maximum Body-Diode Continuous Current	Is				-2.2	Α
Diode Forward Voltage	VsD	Is=-1A,VGS=0V		-0.75	-1	V



#### **Typical Characterisitics**

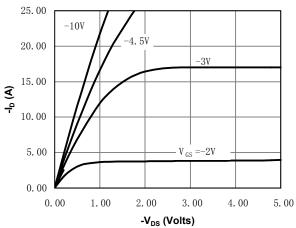


Fig 1: On-Region Characteristics

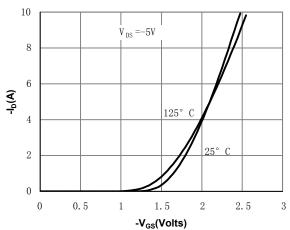


Figure 2: Transfer Characteristics

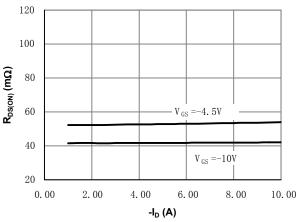


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

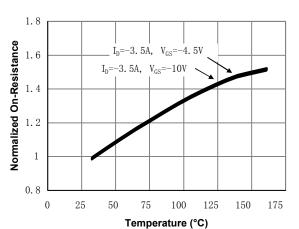


Figure 4: On-Resistance vs. Junction
Temperature

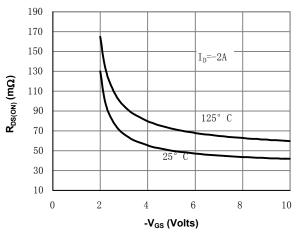


Figure 5: On-Resistance vs. Gate-Source Voltage

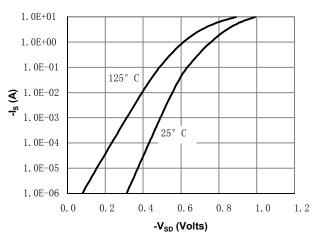


Figure 6: Body-Diode Characteristics



#### **Typical Characterisitics**

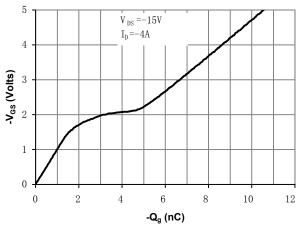


Figure 7: Gate-Charge Characteristics

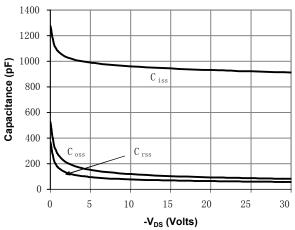


Figure 8: Capacitance Characteristics

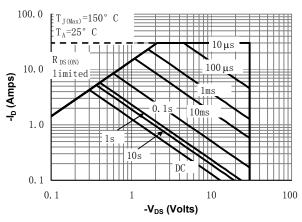


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

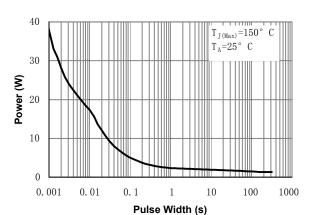


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

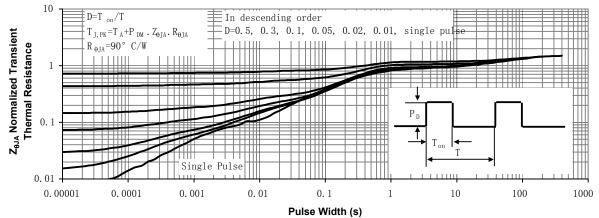
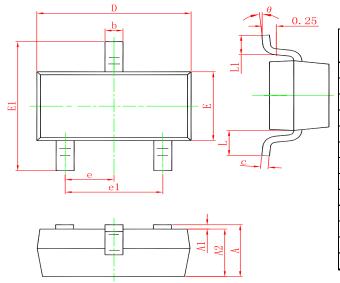


Figure 11: Normalized Maximum Transient Thermal Impedance



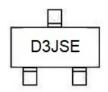
#### **P-Channel MOSFET**

### **SOT-23 PACKAGE OUTLINE DIMENSIONS**



	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP.		0.037 TYP.		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF.		0.022 REF.		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## Marking



# Ordering information

Order code	Package	Baseqty	Deliverymode
UMW SI2323DS	SOT-23	3000	Tape and reel